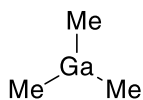


Catalog # 98-2000 Trimethylgallium, elec. gr. (99.9999%-Ga) PURATREM



Thermal Behavior:

- Melting point -15.8°C [1]
 - Boiling point 55.7°C [1]
- Vapor pressure (Torr): 22.0/-20°C; 29.7/-15°C; 39.7/-10°C; 52.4/-5°C;
64.5 /0°C 88.6/5°C; 113.7/10°C; 144.6/15°C;
182.3/20°C; 228.2/25°C; 283.5/30°C

Table is available in [1, 2]

Technical Notes:

- ALD/CVD precursor for Gallium thin film deposition

Target Deposit	Deposition Technique	Delivery Temperature	Pressure	Co-reactants	Deposition Temperature	Ref.
Ga ₂ O ₃	ALD PEALD	RT	1 Torr -	O ₃ ^{PL} O ₂	200-375°C Various temps	3 4-6
GaN	PEALD ALD PEALD	RT	0.25 Torr	^{PL} NH ₃ NH ₃ ^{PL} N ₂ /H ₂ ; Et ₃ Ga	185-385°C 375-425°C 200°C	7 8 9
GaS	PEALD	RT	-	^{PL} H ₂ S/Ar	70-350°C	10
GaAs	ALD	RT	200 Torr	AsH ₃	400°C	11
GaP	ALD ALD PEALD	RT	- 1 Torr	PH ₃ P(NMe ₃) ₃ ^{PL} PH ₃	500°C 400-500°C 380°C	12 13 14
InGaAs	ALD	RT	100 Torr	InMe ₃ , AsH ₃ , H ₂	400-550°C	15
Al _x Ga _{1-x} N	PEALD	6°C	-	AlMe ₃ , ^{PL} NH ₃ or ^{PL} N ₂ /H ₂	200°C	16
In _x Ga _{1-x} N	PEALD	RT	-	InMe ₃ , ^{PL} N ₂ /Ag	350-450°C	17
AlGa _x O _y	ALD	RT	0,5-1 Torr	AlMe ₃ , H ₂ O, O ₃	200°C	18
InGa _x O _y	ALD	RT	-	InMe ₃ , H ₂ O ₂ /H ₂ O	200°C	19

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